

	Typ	L #	Hits	S arch Text	DBs	Tim Stamp
1	BRS	L2	53	densify\$6 near4 (SOG or "spin on glass")	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/15 20:02
2	BRS	L3	289171 88	P or B or In or As or Sb or phophorous or boron or indium or arsenic or antimony	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/15 20:03
3	BRS	L4	53	densify\$6 near4 (SOG or "spin on glass")	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/15 20:03
4	BRS	L5	268411	implant\$6 or inplant\$6	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/15 20:03
5	BRS	L6	105655	solid near2 phase	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/15 20:03

	Type	L #	Hits	Search T xt	DBs	Tim Stamp
6	BRS	L7	1754	"shallow junctions"	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/15 20:03
7	BRS	L8	10660	SOG or "spin on glass" or spin-on-glass	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/15 20:03
8	IS&R	L9	539	(438/96).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/15 20:03
9	IS&R	L10	278	(438/789).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/15 20:03
10	IS&R	L11	683	(438/766).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/15 20:03

	Type	L #	Hits	S arch T xt	DBs	Tim Stamp
11	BRS	L12	302	plasma near2 ion near2 implant\$4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/15 20:03
12	BRS	L13	3	("shallow junctions" same (SOG or "spin on glass" or spin-on-glass)) same (densify\$6 near4 (SOG or "spin on glass")) same densify\$4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/15 20:03
13	BRS	L14	6	(doped adj SOG or doped adj silicon adj glass) and densifying	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/15 20:03
14	BRS	L21	5425	"plasma ion implanter" or "plasma immersion ion implanter" or PIII or "ion shower implanter" or ISI	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/15 20:03
15	BRS	L1	6	(doped adj SOG or doped adj silicon adj glass) and densifying	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/15 20:03

	Typ	L #	Hits	S arch T xt	DBs	Time Stamp
16	BRS	L15	33	(densify\$6 near4 (SOG or "spin on glass")) same (P or B or In or As or Sb or phosphorous or boron or indium or arsenic or antimony)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/15 20:03
17	BRS	L16	4	((densify\$6 near4 (SOG or "spin on glass")) same (P or B or In or As or Sb or phosphorous or boron or indium or arsenic or antimony)) same (implant\$6 or inplant\$6)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/15 20:03
18	BRS	L17	8	(solid near2 phase) near4 "shallow junctions"	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/15 20:03
19	BRS	L18	2	((solid near2 phase) near4 "shallow junctions") and (SOG or "spin on glass" or spin-on-glass)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/15 20:04
20	BRS	L19	24	"shallow junctions" same (SOG or "spin on glass" or spin-on-glass)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/15 20:04

	Type	L #	Hits	Search T xt	DBs	Time Stamp
21	BRS	L20	2	("shallow junctions" same (SOG or "spin on glass" or spin-on-glass)) and (plasma near2 ion near2 implant\$4)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/15 20:04
22	BRS	L22	55	(SOG or "spin on glass" or spin-on-glass) and ("plasma ion implanter" or "plasma immersion ion implanter" or PIII or "ion shower implanter" or ISI)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/15 20:04
23	BRS	L23	1	(SOG or "spin on glass" or spin-on-glass) same ("plasma ion implanter" or "plasma immersion ion implanter" or PIII or "ion shower implanter" or ISI)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/15 20:04